

BYC10MD-650P

## Hyperfast power diode

Rev.01 - 25 October 2022

**Product data sheet** 

#### **1. General description**

Hyperfast power diode in a TO252 (DPAK) plastic package.



#### 2. Features and benefits

- Low leakage current
- Low thermal resistance
- Low reverse recovery current
- Reduces switching losses in associated MOSFET or IGBT

#### **3. Applications**

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

#### 4. Quick reference data

Table 1. Q	uick reference data						
Symbol	Parameter	Conditions	Notes	Values			Unit
Absolute	maximum rating						
$V_{\text{RRM}}$	repetitive peak reverse voltage				650		V
$I_{F(AV)}$	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 136 °C; Fig. 1; Fig. 2; Fig. 3		10			A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 136 °C; square-wave pulse		20			A
I <sub>FSM</sub> non-repetitive peak forward current		$t_{\rm p}$ = 10 ms; $T_{\rm j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		135		A	
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse			148		А
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.40	3.20	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.50	2.30	V
Dynamic	characteristics						
t <sub>rr</sub>	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	13	-	ns

### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol		
1	n.c.	not connected		К-Ң-А		
2	K	cathode [1]		001aaa020		
3	A	anode				
mb	К	mounting base; connected to cathode				

[1] It is not possible to connect to pin 2 of the TO252 package.

### **6. Ordering information**

Table 3. Ordering information								
Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BYC10MD-650P	TO252	BYC10MD-650PJ	Reel	2500	TO252d	07-Sep-2022		

#### 7. Marking

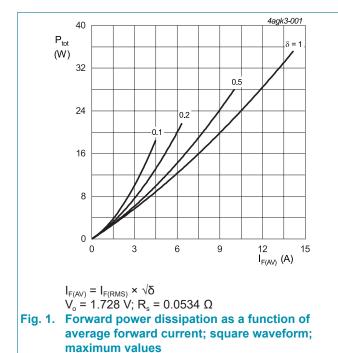
Table 4. Marking codes						
Type number	Marking codes					
BYC10MD-650P	BYC10MD 650P					

#### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage			650	V
$V_{\text{RWM}}$	crest working reverse voltage			650	V
V <sub>R</sub>	reverse voltage	DC		650	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; square-wave pulse; T <sub>mb</sub> ≤ 136 °C; Fig. 1; Fig. 2; Fig. 3		10	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 136 °C; square-wave pulse		20	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; Fig. 4		135	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse		148	А
T <sub>stg</sub>	storage temperature			-65 to 175	°C
T <sub>j</sub>	junction temperature			-65 to 175	°C

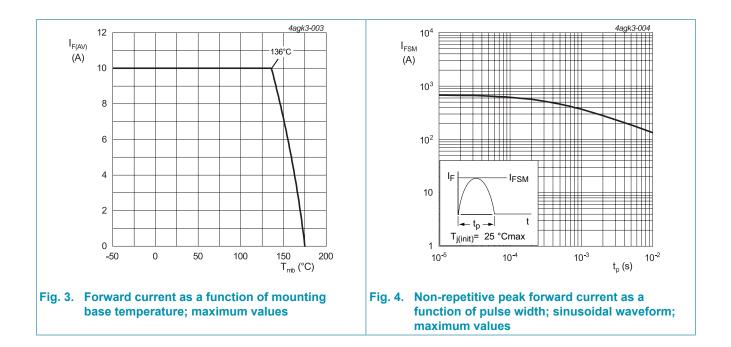


4agk3-002 30  $\mathsf{P}_{\mathrm{tot}}$ 1.57 (W) 1.9 24 2.2 28 18 <u>4</u> N 12 6 0 2 4 6 0 8 10  $I_{F(AV)}$  (A) a = form factor = I\_{F(RMS)} / I\_{F(AV)} V\_{o} = 1.728 V; R\_s = 0.0534  $\Omega$ 

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

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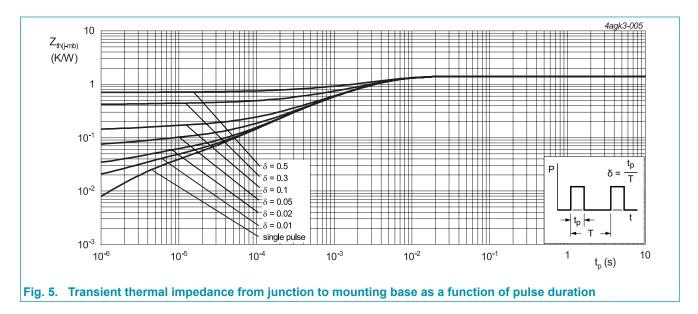
BYC10MD-650P



## 9. Thermal characteristics

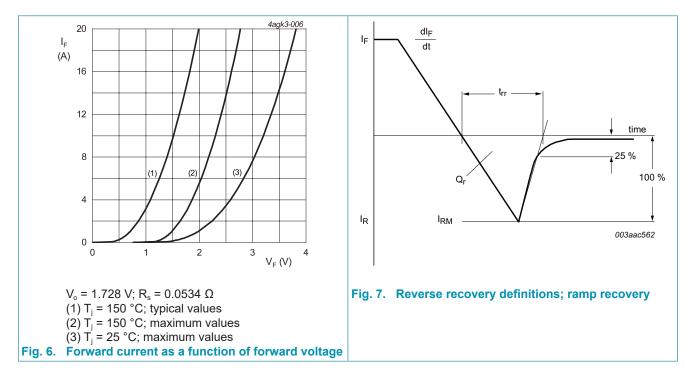
Table 6. Th	ermal characteristics						
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	[2]	-	50	-	K/W

[2] Device mounted on an FR4 PCB, single-sided copper, tin plated and standard footprint.

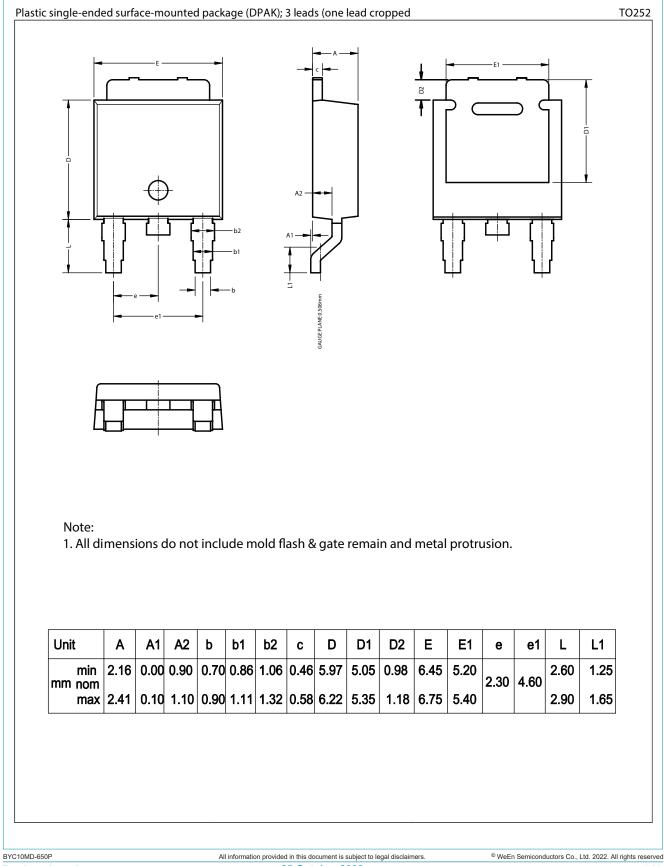


### **10. Characteristics**

	haracteristics	a			-		
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 10 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>		-	2.40	3.20	V
		I <sub>F</sub> = 10 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>		-	1.50	2.30	V
R	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C		-	0.5	30	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 150 °C		-	0.1	0.8	mA
Dynamic	characteristics						
Q <sub>r</sub>	reverse charge	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	37	-	nC
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	115	-	nC
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 1 \text{ A}; I_{rr} = 0.25 \text{ A}; T_j = 25 \text{ °C}$		-	20	-	ns
		$I_F = 1 \text{ A}; V_R = 30 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	13	-	ns
		$I_F$ = 10 A; $V_R$ = 200 V; $dI_F/dt$ = 200 A/µs; $T_j$ = 25 °C; Fig. 7		-	29	-	ns
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	48	-	ns
I <sub>RM</sub>	peak reverse recovery currentnon-repetitive avalanche energy	$I_F = 10 \text{ A}; V_R = 200 \text{ V}; \text{ d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 25 \text{ °C}; \text{ Fig. 7}$		-	2.6	-	A
		$I_F = 10 \text{ A}; V_R = 200 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; Fig. 7$		-	4.8	-	A
as	non-repetitive avalanche energy	T <sub>j(init)</sub> = 25 °C		10.8	-	-	mJ



#### 11. Package outline



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#### Hyperfast power diode

## 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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